C385V-110

UV LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	InGaN on Si Substrate
p-pad Electrode	AuSn Alloy
n-pad Electrode	Au Alloy
Chip Size	1067umx1067um typical
Chip Thickness	150um typical
Pad Diameter	150umx150um typical

Absolute Maximum Ratings[Ta=25℃]

Item	Symbol	Maximum Rated Value	Unit
Forward Current	IF	1000	mW
	IFP*	1200	mA
Reverse Voltage	VR	5	V
Junction Temperature	Tj	125	K/W
Operating Temperature	TOPR	-40 ~ +85	℃
Storage Temperature	TSTG	-20 ~ +65	℃

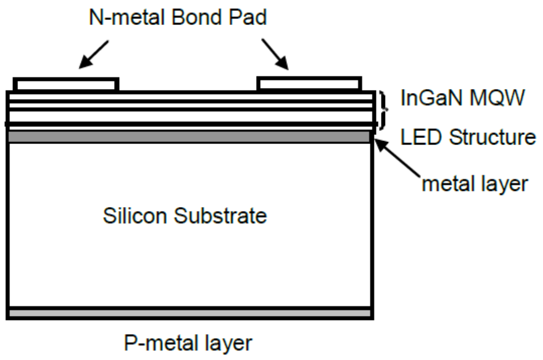
* Pulse Forward Current condition: Duty=1%xPulse Width=10us

Electro-Optical Characteristics [Ta=25℃ typ.]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=500mA	3.2	3.5	4.0	V
Radiated Power	PO	IF=500mA		800		uA
Peak Wavelength	λP	IF=500mA	380	385	390	nm
FWHM	Δλ	IF=500mA		14		nm

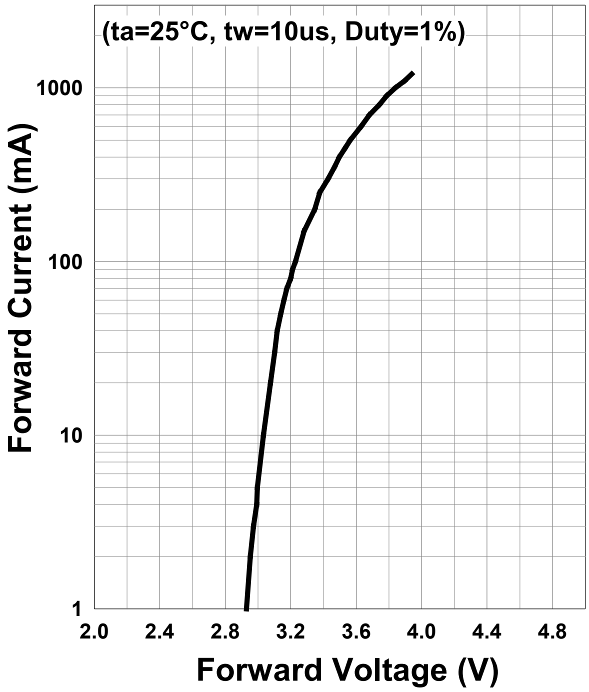
Die shall be mounted on TO-18 gold header without resin coated. (Ta=25℃)

<Chip Diagram>

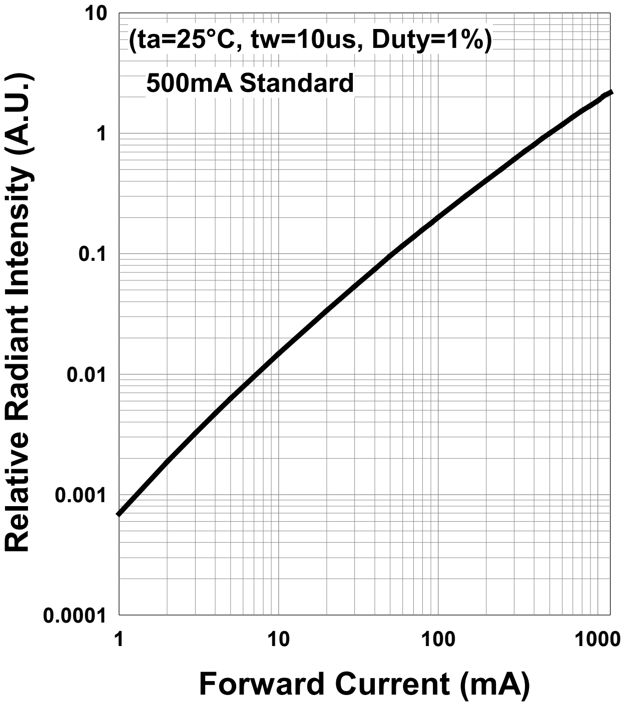


Chip Side view

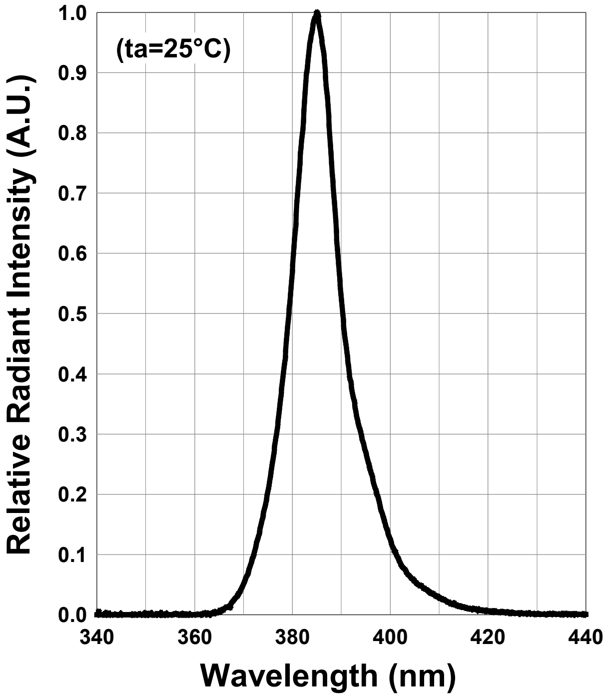
Forward Curent - Forward Voltage



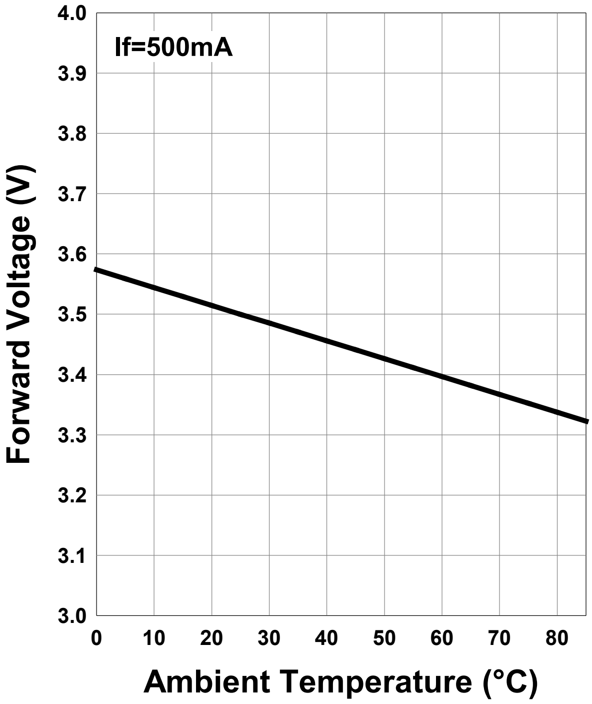
Relative Radiant Intensity - Forward Current



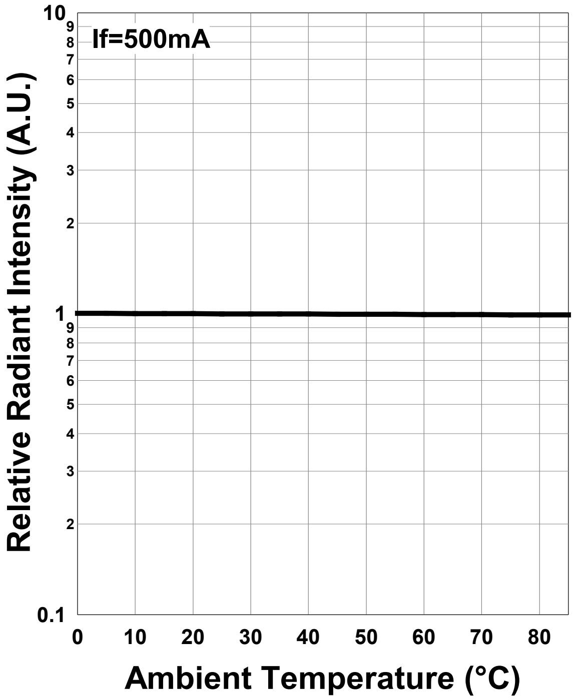
Relative Spectral Emission



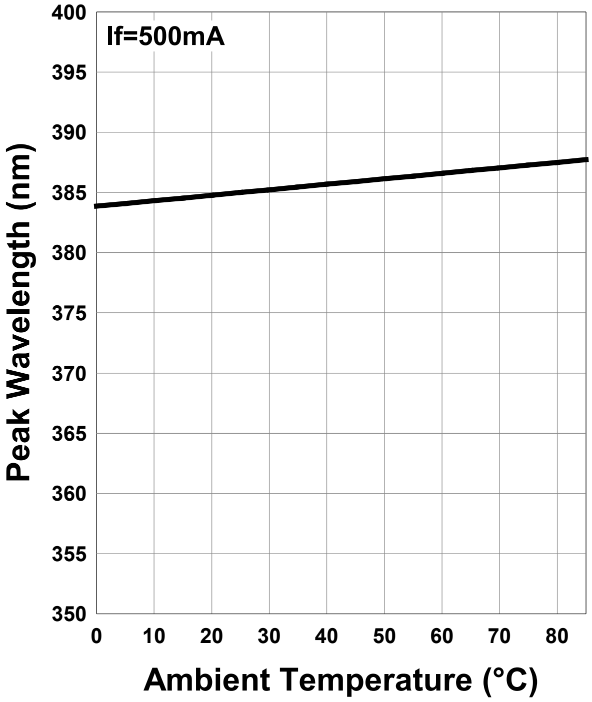
Forward Voltage - Ambient Temperature



Relative Radiant Intensity - Ambient Temperature



Peak Wavelength - Ambient Temperature



Disclaimer

Product specifications and data shown in this product catalog are subject to change without notice for the purposes of improving product performance, reliability, design, or otherwise.

Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements. Product data and parameters may vary by user application and over time.

Products shown in this catalog are intended to be used for general electronic equipment. Products are not guaranteed for applications where product malfunction or failure may cause personal injury or death, including but not limited to life-supporting / saving devices, medical devices, safety devices, airplanes, aerospace equipment, automobiles, traffic control systems, and nuclear reactor control systems.

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